

Supporting Information

Realization of an efficient electron source by ultraviolet-light-assisted field emission from a one-dimensional ZnO nanorods/n-GaN heterostructure photoconductive detector

*Yiren Chen, ^{a,†} Zhiwei Zhang, ^a Hong Jiang, ^a Zhiming Li, ^a Guoqing Miao, ^a Hang Song, ^{*a} Liqin Hu,
^{b,†} and Tailiang Guo ^{*b}*

^a State Key Laboratory of Luminescence and Applications, Changchun Institute of Optics, Fine Mechanics and Physics, Chinese Academy of Sciences, Changchun 130033, People's Republic of China

^b College of Physics and Information Engineering, Fuzhou University, Fuzhou 350002, People's Republic of China

[†] These authors contributed equally.

Corresponding Author

*E-mail: songh@ciomp.ac.cn

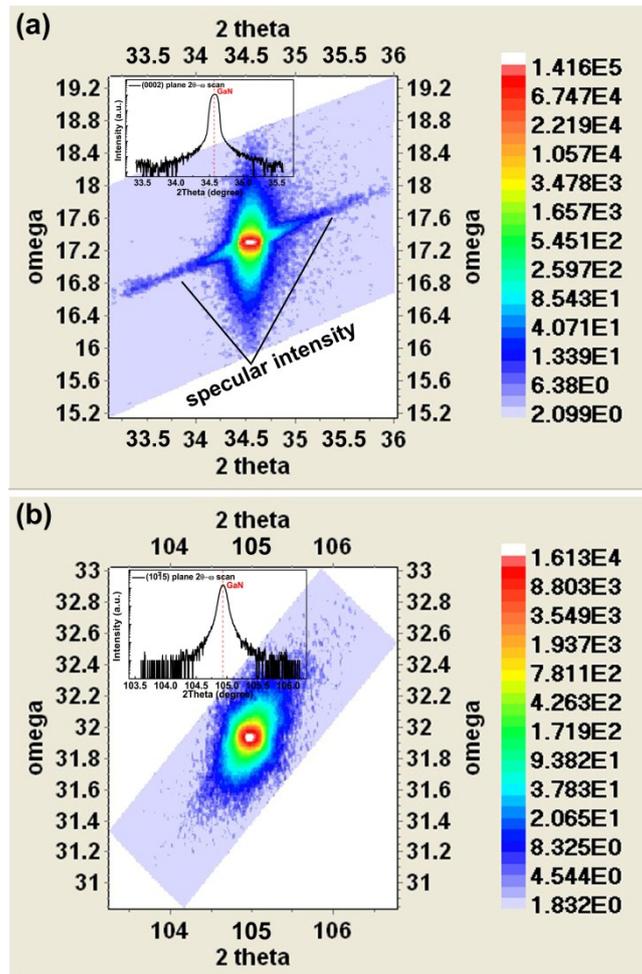


Fig. S1. Reciprocal space mapping (RSM) obtained by a high-resolution X-ray diffractometer. (a) The symmetrical RSM around the (0002) reflection for as-fabricated n-GaN epilayer. The inset shows its corresponding 2θ - ω scanning curve. (b) The asymmetrical RSM around the (105) reflection for as-fabricated n-GaN epilayer. The inset shows its corresponding 2θ - ω scanning curve.